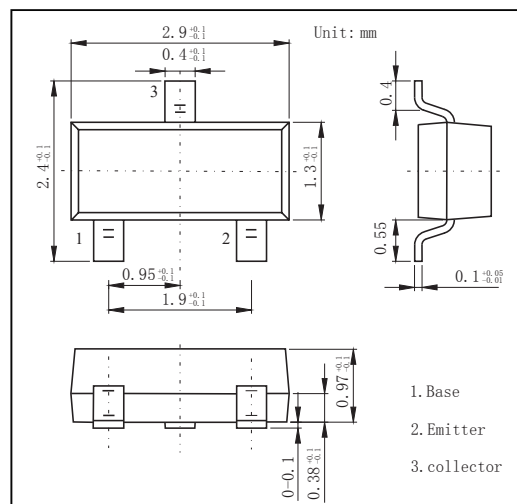


SOT-23 Plastic-Encapsulate Transistors
Features

- For general amplification
-
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector - Base Voltage	V _{CBO}	-45	V
Collector - Emitter Voltage	V _{CEO}	-45	
Emitter - Base Voltage	V _{EBO}	-7	
Collector Current - Continuous	I _C	-100	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E =0	-45			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -2 mA, I _B =0	-45			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C =0	-7			
Collector-base cut-off current	I _{CBO}	V _{CB} = -40 V, I _E =0			-0.1	μA
Collector-Emitter cut-off current	I _{CEO}	V _{CE} = -20 V, I _B =0			-100	
Emitter cut-off current	I _{EBO}	V _{EB} = -6V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100 mA, I _B =-10mA			-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-100 mA, I _B =-10mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -10V, I _C = -2mA	160		460	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0,f=1MHz			2.7	pF
Transition frequency	f _T	V _{CE} = -10V, I _C = -1mA,f=200MHz	60			MHz

RATINGS AND CHARACTERISTIC CURVES

